

TPNTA4153NT1G

N-Channel Enhancement Mode MOSFET

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Features

- $V_{DS} = 20V, I_D = 0.8A$ $R_{DS(ON)} < 250m \Omega @ V_{GS} = 4.5V$ $R_{DS(ON)} < 300m \Omega @ V_{GS} = 2.5V$
- ESD Protection

Package and Pin Configuration

Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable
 Electronics
- Logic Level Shift

Go

Circuit diagram



SOT-523

marking: A

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±8	V
Continuous Drain Current	Ι _D	0.8	A
Pulsed Drain Current (t=300µs) ⁽¹⁾	I _{DM}	1.8	A
Power Dissipation (2)	PD	280	mW
Thermal Resistance from Junction to Ambient	R _{eja}	452	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C



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Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Туре	Max	Unit
Static Characteristics	•					
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250µA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	$V_{GS} = \pm 8 V, V_{DS} = 0 V$			±10	μA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.5	0.75	1.1	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =4.5V, I _D =550mA		180	250	mΩ
		V _{GS} = 2.5V I _D = 450mA		230	300	11132
Forward tranconductance	g fs	V _{DS} =5 V, I _D =500mA		1.7		S
Dynamic characteristics ⁽⁴⁾	- 1					
Input Capacitance	C _{iss}				120	
Output Capacitance	Coss	V_{DS} = 16V, V_{GS} = 0V, f = 1MHz			20	pF
Reverse Transfer Capacitance	Crss				15	5
Switching Characteristics ⁽⁴⁾			·		•	
Turn-on delay time	t _{d(on)}			6.7		
Turn-on rise time	tr	V _{DD} =10V,I _D =500mA,		4.8		-
Turn-off delay time	t _{d(off)}	V _{GS} =4.5V,R _G =10Ω		17.3		ns
Turn-off fall time	t _f	1		7.4		
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	I _S =0.15A, V _{GS} = 0V			1.2	V

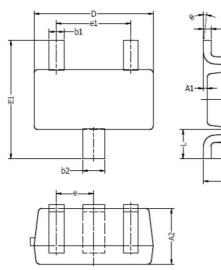


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SOT523 Package Outline Drawing



Suggested	Land	Pattern
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DIM -	MILLIM	ETERS	INCH	IES
	MIN	MAX	MIN	MAX
А	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
с	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
Е	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
е	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0 °	8 °	0 °	8 °



Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
 Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

